

2021 02 09

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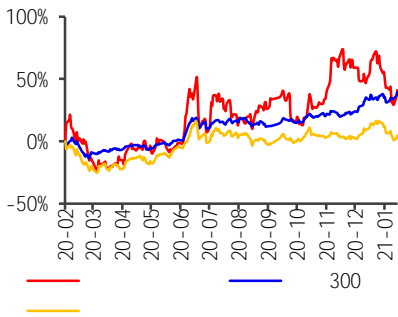
59.21  
719.95  
147.46  
121,593  
24,904  
12 / 74.89/31.74

S1070518060001

☎ 021-31829706  
✉ zoulalan@cgws.com

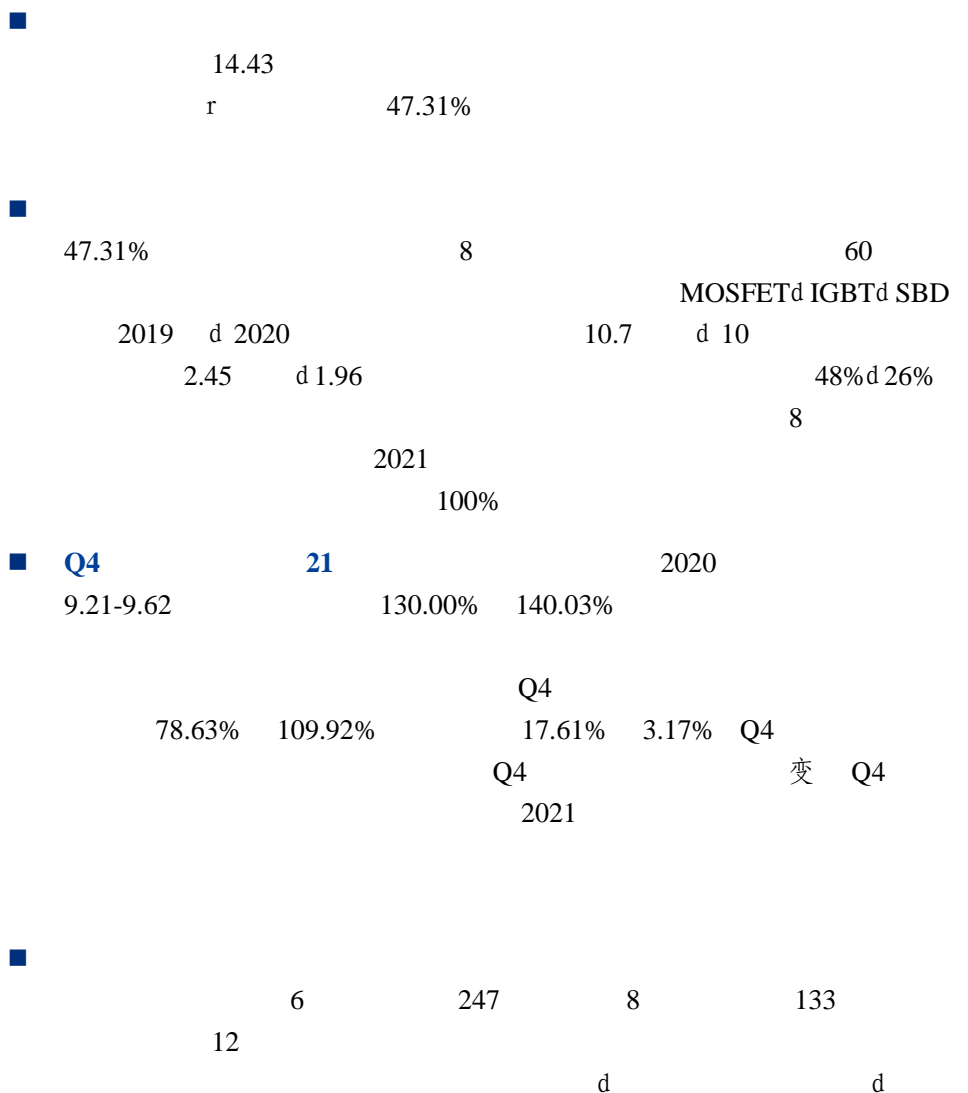
S1070119070022

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688396

	2018A	2019A	2020E	2021E	2022E
(+/-%)	6271	5743	6788	8605	9982
(+/-%)	6.7%	-8.4%	18.2%	26.8%	16.0%
EPS	429	401	936	1598	1894
(+/-%)	511.0%	-6.7%	133.5%	70.8%	18.5%
PE	0.35	0.33	0.77	1.31	1.56
	164	176	75	46	40



-100V	1500V	d	d	MOSFET	IGBT
		2020		IGBT	
	70%			1	
	2020	SiC		比	d
d				SiC MOSFET	GaN
			d		
■	r			IDM	
	层		d		
		2020-2022		9.36	d 15.98
d 18.94	EPS	0.77	d 1.31	d 1.56	PE
■			d		



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